CMXD4448

SURFACE MOUNT TRIPLE ISOLATED HIGH SPEED SILICON SWITCHING DIODES





www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD4448 type contains three (3) Isolated High Speed Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for applications requiring high speed switching.

MARKING CODE: X48

MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
Continuous Reverse Voltage	V_{R}	75	V
Peak Repetitive Reverse Voltage	V _{RRM}	100	V
Continuous Forward Current	ΙF	250	mA
Peak Repetitive Forward Current	I _{FRM}	500	mA
Peak Forward Surge Current, tp=1.0µs	I _{FSM}	4.0	Α
Peak Forward Surge Current, tp=1.0s	I _{FSM}	1.0	Α
Power Dissipation	P_{D}	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	ΘιΛ	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

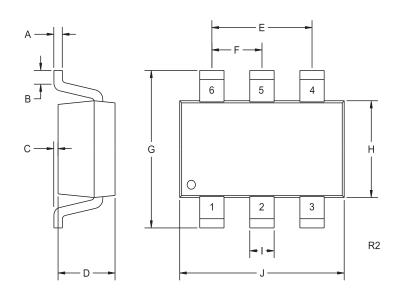
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{R}	V _R =20V		25	nA
BV_R	I _R =5.0μA	75		V
BV_R	I _R =100μA	100		V
V_{F}	I _F =100mA		1.0	V
C_T	V _R =0, f=1.0MHz		4.0	pF
t _{rr}	$I_R=I_F=10$ mA, $I_{rr}=1.0$ mA, $R_L=100$ Ω		4.0	ns

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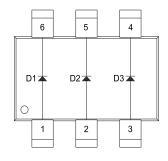
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SOT-26 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
Α	0.004	0.007	0.11	0.19			
В	0.016	-	0.40	-			
C	-	0.004	-	0.10			
D	0.039	0.047	1.00	1.20			
E	0.074	0.075	1.88	1.92			
F	0.037	0.038	0.93	0.97			
G	0.102	0.118	2.60	3.00			
Ι	0.059	0.067	1.50	1.70			
	0.016		0.41				
J	0.110	0.118	2.80	3.00			

SOT-26 (REV: R2)

LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

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R5 (12-February 2010)